P-Channel 30-V (D-S) MOSFET

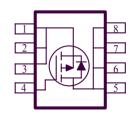
These miniature surface mount MOSFETs utilize High Cell Density process. Low r_{DS(on)} assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

•	Low r _{DS(on)} Provides Higher Efficiency and
	Extends Battery Life

- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (±25) for battery pack applications

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$	
-30	$30 @ V_{GS} = -10V$	9.5	
-30	$52 @ V_{GS} = -4.5V$	7.5	





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage			-30	V		
Gate-Source Voltage			±25	V		
Continuous Drain Current ^a	$T_A=25^{\circ}C$	Ι	9.5			
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1D	8.3	A		
Pulsed Drain Current ^b			±50			
Continuous Source Current (Diode Conduction) ^a	I_S	-2.1	A			
D Dii4ia	$\frac{T_A=25^{\circ}C}{T_A=70^{\circ}C}P_D$		3.1	W		
Power Dissipation ^a	$T_A=70^{\circ}C$	1 D	2.6	**		
Operating Junction and Storage Temperature Range		T_{J}, T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	50	°C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Dayarra to v	Cl1	T (C P)	Limits			TT •4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \text{ uA}$	-30			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1	-1.6	-3	V	
Gate-Body Leakage	Igss	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Gurrant	IDSS	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			A	
		$V_{GS} = -10 \text{ V}, I_D = -9.5 \text{ A}$		24	30		
Drain-Source On-Resistance ^A	fDS(on)	$V_{GS} = -4.5 \text{ V}, I_D = -7.5 \text{ A}$		44	52	mΩ	
		$V_{GS} = -10 \text{ V}, I_D = -9.5 \text{ A}, TJ = 55^{\circ}\text{C}$		29	36		
Forward Tranconductance ^A	gs	$V_{DS} = -15 \text{ V}, I_D = -9.5 \text{ A}$		31		S	
Diode Forward Voltage	V _{SD}	$I_S = -2.1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.7	-1.2	V	
Dynamic ^b	·						
Total Gate Charge	Qg	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V},$ $I_{D} = -9.5 \text{ A}$		15	26		
Gate-Source Charge	Qgs			5.8		nC	
Gate-Drain Charge	Qgd			12			
Switching							
Turn-On Delay Time	t _{d(on)}			15	26		
Rise Time	$t_{\rm r}$	$V_{DD} = -15 \text{ V}, R_L = 15 \Omega, ID = -1 \text{ A},$		12	21	nS	
Turn-Off Delay Time	td(off)	$VGEN = -10 V$, $RG = 6\Omega$		62	108	113	
Fall-Time	t_{f}			46	71		

Notes

- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (P-Channel)

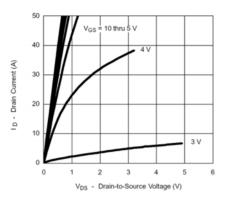


Figure 1. On-Region Characteristics

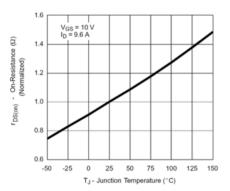


Figure 3. On-Resistance Variation with Temperature

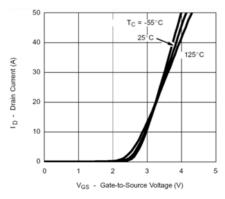


Figure 5. Transfer Characteristics

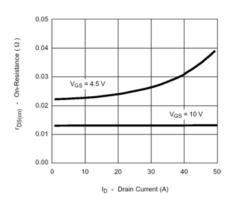


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

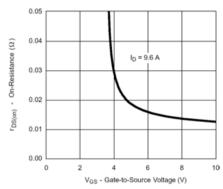


Figure 4. On-Resistance Variation with Gate to Source Voltage

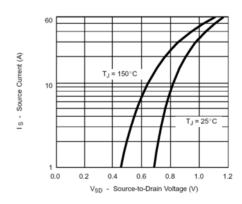


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (P-Channel)

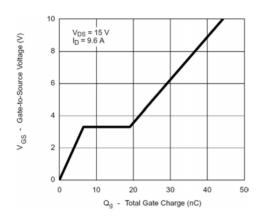


Figure 7. Gate Charge Characteristics

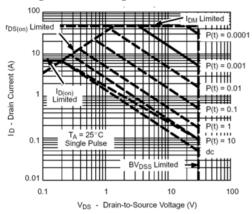


Figure 9. Maximum Safe Operating Area

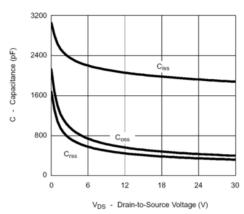


Figure 8. Capacitance Characteristics

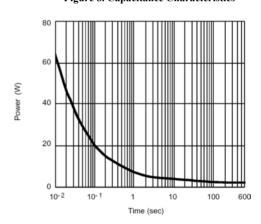
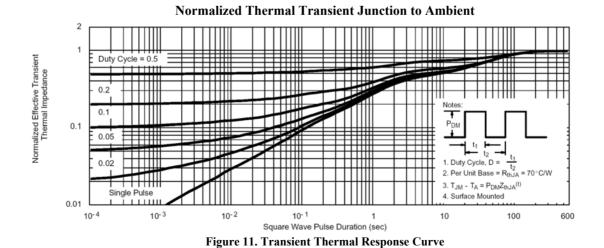
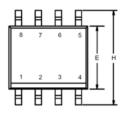


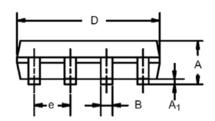
Figure 10. Single Pulse Maximum Power Dissipation



Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

